



Monolayer hBN

hBN Coverage: 100% with sporadic adlayers (see optical image above)

Bandgap: 5.97 eV

Grain size: >4 μm

Raman Peak: 1370 /cm-1

Substrate

Our 8-inch (200mm) Si/SiO₂ wafers are sourced from a reliable, quality-assured supplier.

Type/Doping: P/B

Wafer Thickness : 725 +/- 25μm

Oxide Thickness: 300nm

Resistivity: 5 – 30 (ohm-cm)

Orientation: <1-0-0>

Metal Impurities: 1.00e10 – 5.00e10 (at/cm²)